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FIG.1: Power dissipation vs. on-state current

(per thyristor or diode)

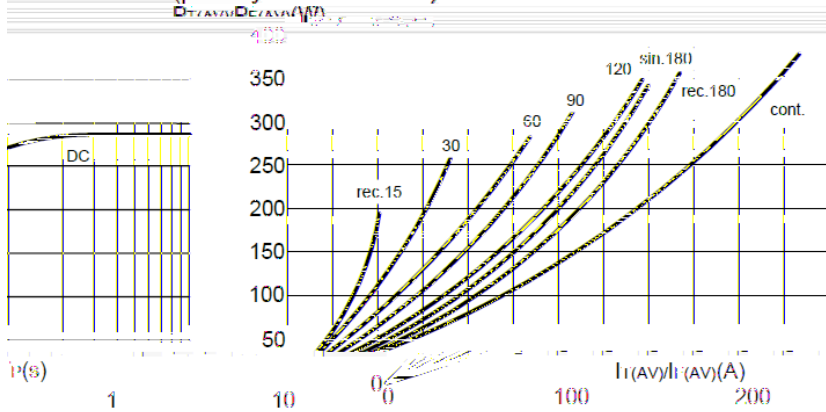


FIG.2: Maximum transient thermal impedance

junction-to-case(per thyristor or diode)

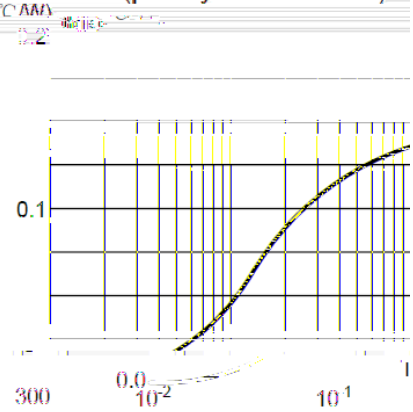


FIG.3: Forward characteristics

(per thyristor or diode)

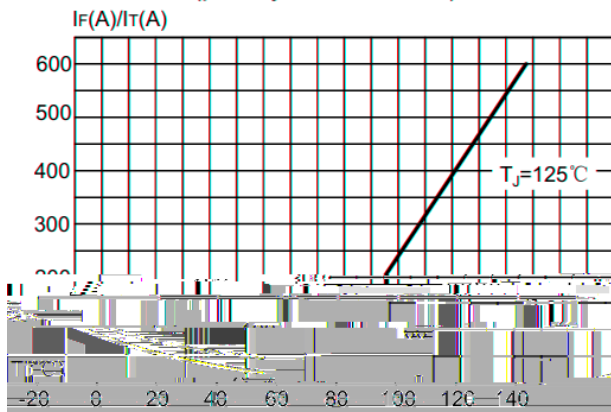


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature

$I_{GT}, I_H, I_L(T_J)/I_{GT}, I_H, I_L(T_J=25^\circ\text{C})$

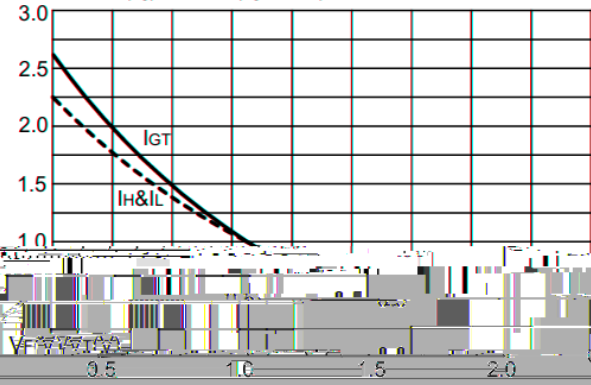


FIG.5: Gate trigger characteristics

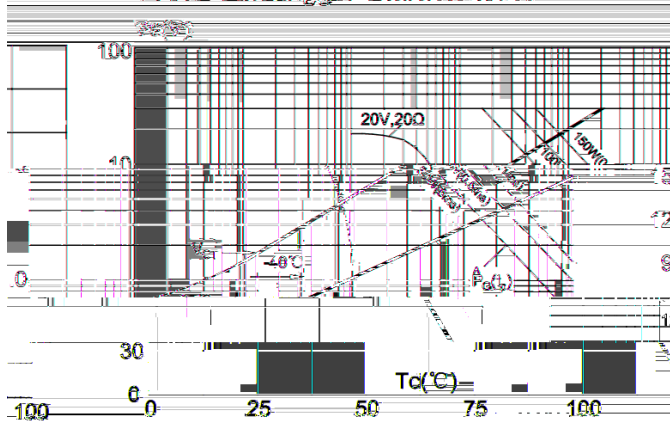


FIG.6: Forward current vs. case temperature

